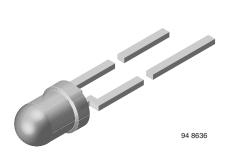
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www.vishay.com

# Vishay Semiconductors

# High Speed Infrared Emitting Diode, 850 nm, Surface Emitter Technology



# DESCRIPTION

VSLY3850 is an infrared, 850 nm emitting diode based on GaAlAs surface emitter chip technology with extreme high radiant intensity, high optical power and high speed, molded in a clear, untinted T1 plastic package.

#### **FEATURES**

· Package type: leaded

• Package form: T-1, clear epoxy

• Dimensions: Ø 3 mm

• Peak wavelength:  $\lambda_p = 850 \text{ nm}$ 

· High speed

• High radiant power

High radiant intensity

• Angle of half intensity:  $\phi = \pm 18^{\circ}$ 

• Suitable for high pulse current operation

• Good spectral matching with CMOS cameras

 Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### Note

\*\* Please see document "Vishay Material Category Policy": www.vishav.com/doc?99902

#### **APPLICATIONS**

- Infrared radiation source for operation with CMOS cameras
- · High speed IR data transmission
- 3D TV application
- Light curtains

PRODUCT SUMMARY					
COMPONENT	I <sub>e</sub> (mW/sr)	φ (deg)	λ <sub>p</sub> (nm)	t <sub>r</sub> (ns)	
VSLY3850	70	± 18	850	10	

#### Note

· Test conditions see table "Basic Characteristics"

ORDERING INFORMATION						
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM			
VSLY3850	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1			

#### Note

· MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1	А	
Power dissipation		P <sub>V</sub>	190	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	300	K/W	





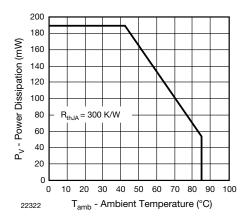


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

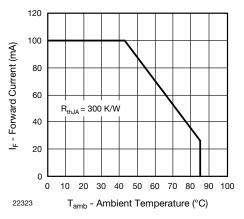


Fig. 2 - Forward Current Limit vs. Ambient Temperature

<b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>		1.65	1.9	V
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>		2.9		V
Townsent we coefficient of V	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>		- 1.45		mV/K
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 10 mA	TK <sub>VF</sub>		- 1.25		mV/K
Reverse current		I <sub>R</sub>	not designed for reverse operation		μΑ	
Junction capacitance	$V_R = 0 \text{ V, f} = 1 \text{ MHz,}$ $E = 0 \text{ mW/cm}^2$	CJ		125		pF
Dadinatintansita	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l <sub>e</sub>	35	70	105	mW/sr
Radiant intensity	$I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$	I <sub>e</sub>		600		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фе		55		mW
Temperature coefficient of radiant power	I <sub>F</sub> = 1 mA	$TK_{\phie}$		- 0.35		%/K
Angle of half intensity		φ		± 18		deg
Peak wavelength	I <sub>F</sub> = 30 mA	λρ	840	850	870	nm
Spectral bandwidth	I <sub>F</sub> = 30 mA	Δλ		30		nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 30 mA	$TK_{\lambdap}$		0.25		nm
Rise time	I <sub>F</sub> = 100 mA, 20 % to 80 %	t <sub>r</sub>		10		ns
Fall time	I <sub>F</sub> = 100 mA, 20 % to 80 %	t <sub>f</sub>		10		ns

## **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

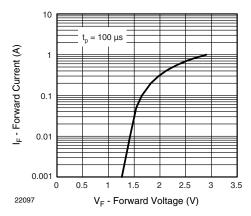


Fig. 3 - Forward Current vs. Forward Voltage

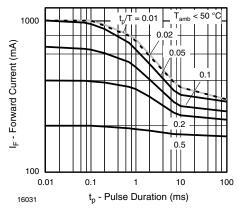


Fig. 4 - Pulse Forward Current vs. Pulse Duration

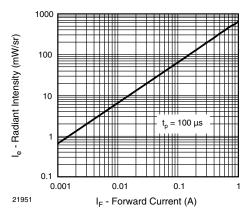


Fig. 5 - Radiant Intensity vs. Forward Current

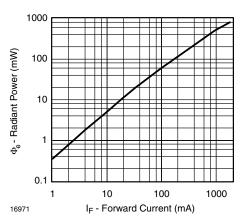


Fig. 6 - Radiant Power vs. Forward Current

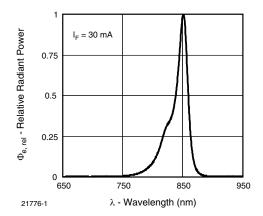


Fig. 7 - Relative Radiant Power vs. Wavelength

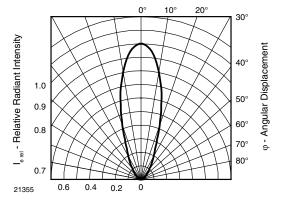
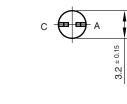
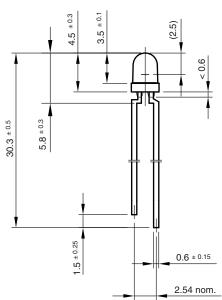


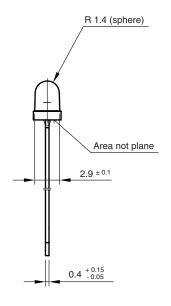
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

# Vishay Semiconductors

### **PACKAGE DIMENSIONS** in millimeters









technical drawings according to DIN specifications

Drawing-No.: 6.544-5264.01-4

Issue: 2; 23.04.98

95 10951





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